

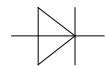
Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

Periodische Spitzenspannung repetitive peak reverse voltage	f = 50Hz	V _{RRM}	-40°C... t _{vj max}	0°C... t _{vj max}	
			3200	3300	V
			3600	3700	V
			4000	4100	V
			4200	4300	V
Durchlaßstrom-Grenzeffektivwert RMS forward current		I _{FRMSM}	8300		A
Dauergrenzstrom mean forward current	t _C = 100°C, f = 50Hz	I _{FAVM}	3700		A
	t _C = 60°C, f = 50Hz		5300		A
Stoßstrom-Grenzwert surge forward current	t _{vj} = 25°C, t _p = 10ms	I _{FSM}	70		kA
	t _{vj} = t _{vj max} , t _p = 10ms		56		kA
Grenzlastintegral I ² t-value	t _{vj} = 25°C, t _p = 10ms t _{vj} = t _{vj max} , t _p = 10ms	I ² t	25,5·10 ⁶		A ² s
			15,68·10 ⁶		A ² s

Charakteristische Werte / Characteristic values

Durchlaßspannung forward voltage	t _{vj} = t _{vj max} , I _F = 4000A	V _F	max	1,27	V
Schleusenspannung threshold voltage	t _{vj} = t _{vj max}	V _(TO)	typ 0,69	max 0,76	V
Ersatzwiderstand forward slope resistance	t _{vj} = t _{vj max}	r _T	typ 0,127	max 0,128	mΩ
Durchlaßrechenkennlinie On-state characteristics for calculation $V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$	t _{vj} = t _{vj max}	A B C D	typ. 0,580 0,0000170 -0,0255 0,0121		
Durchlaßrechenkennlinie On-state characteristics for calculation $V_F = A + B \cdot i_F + C \cdot \ln(i_F + 1) + D \cdot \sqrt{i_F}$	t _{vj} = t _{vj max}	A B C D	max. 0,641 0,0000262 -0,0390 0,0166		
Sperrstrom reverse current	t _{vj} = t _{vj max} , V _R = V _{RRM}	i _R	200		mA
Rückstromspitze peak reverse recovery current	t _{vj} = t _{vj max} I _{FM} = 1500A, -di/dt = 5 A/μs V _R = 0,5 V _{RRM} , C = 4,7μF, R = 8,2Ω	I _{RM}	200		A
Sperrverzögerungsladung recovered charge	t _{vj} = t _{vj max} I _{FM} = 1500A, -di/dt = 5 A/μs V _R = 0,5 V _{RRM} , C = 4,7μF, R = 8,2Ω	Q _r	max	7,2	mAs



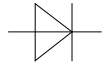
Thermische Eigenschaften / Thermal properties

Innerer Wärmewiderstand thermal resistance, junction to case	beidseitig / two-sided, DC Anode / anode, DC Kathode / cathode, DC	R_{thJC}	max max max	0,0085 0,016 0,018	$^{\circ}C/W$ $^{\circ}C/W$ $^{\circ}C/W$
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	Kühlfläche / cooling surface beidseitig / two-sided einseitig / single sided	R_{thCK}	max max	0,0025 0,005	$^{\circ}C/W$ $^{\circ}C/W$
Höchstzulässige Sperrschichttemperatur max. junction temperature		$t_{vj \max}$		160	$^{\circ}C$
Betriebstemperatur operating temperature		$t_{c \text{ op}}$		-40...+160	$^{\circ}C$
Lagertemperatur storage temperature		t_{stg}		-40...+160	$^{\circ}C$

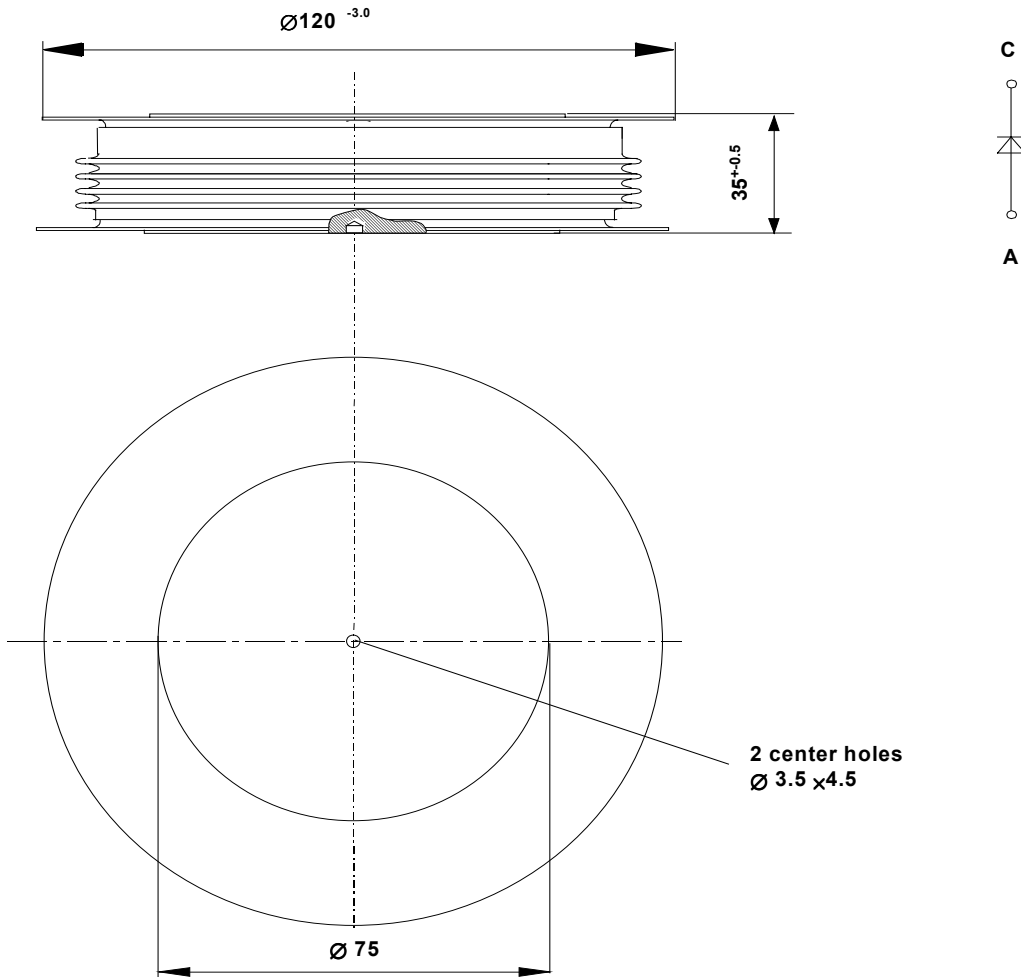
Mechanische Eigenschaften / Mechanical properties

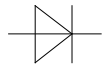
Gehäuse, siehe Anlage case, see appendix				Seite 3	
Si - Element mit Druckkontakt Si - pellet with pressure contact				75DN42	
Anpreßkraft clamping force		F		36...52	kN
Gewicht weight		G	typ	1700	g
Kriechstrecke creepage distance				40	mm
Luftstrecke air distance				30	mm
Feuchtklasse humidity classification	DIN 40040			C	
Schwingfestigkeit vibration resistance	f = 50Hz			50	m/s^2

Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.
This technical Information specifies semiconductor devices but promises no characteristics. It is valid in combination with the belonging technical notes.



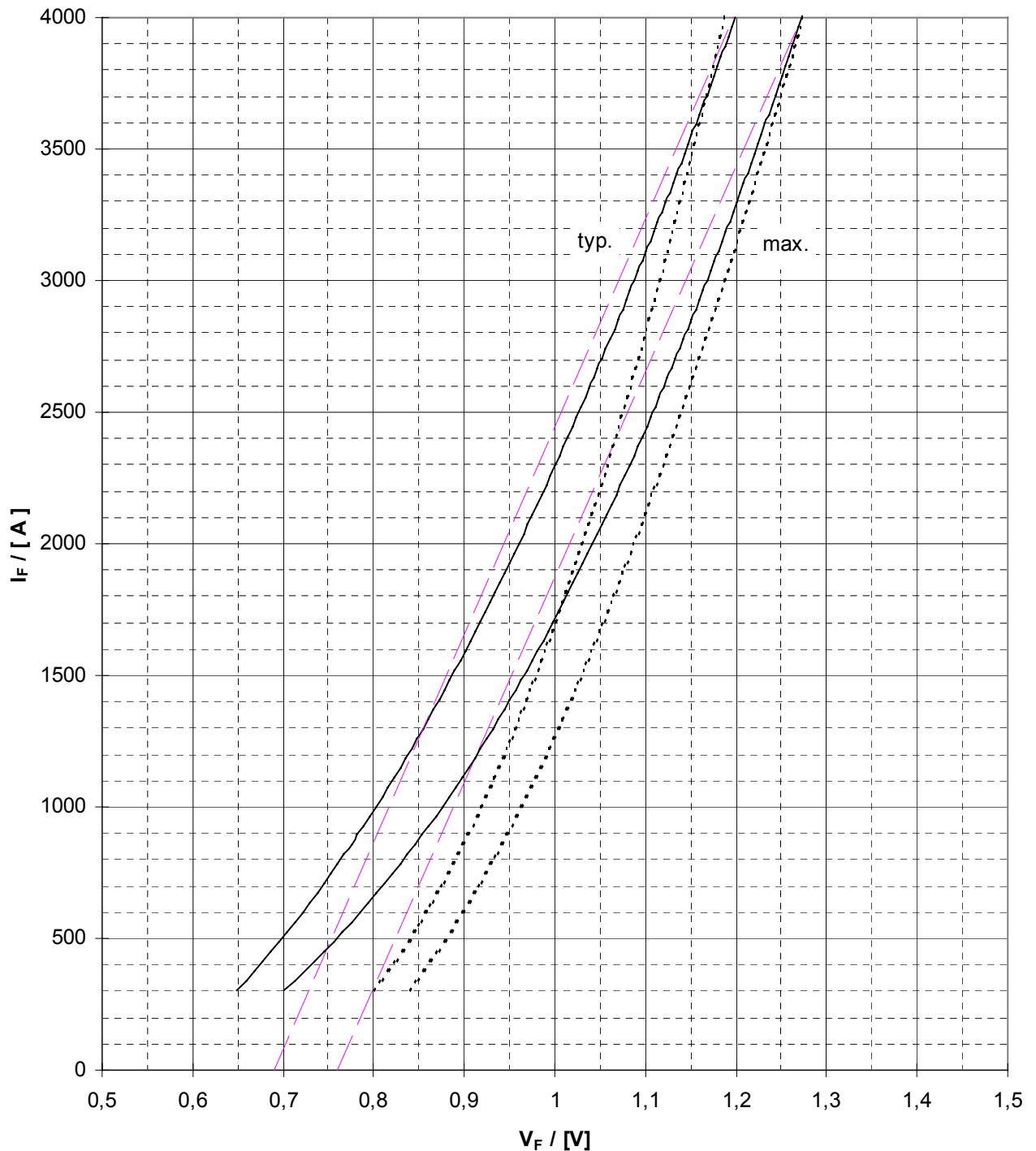
Maßbild / Outline

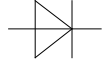




On-State Characteristics (v_F)
typical and limiting on state characteristic

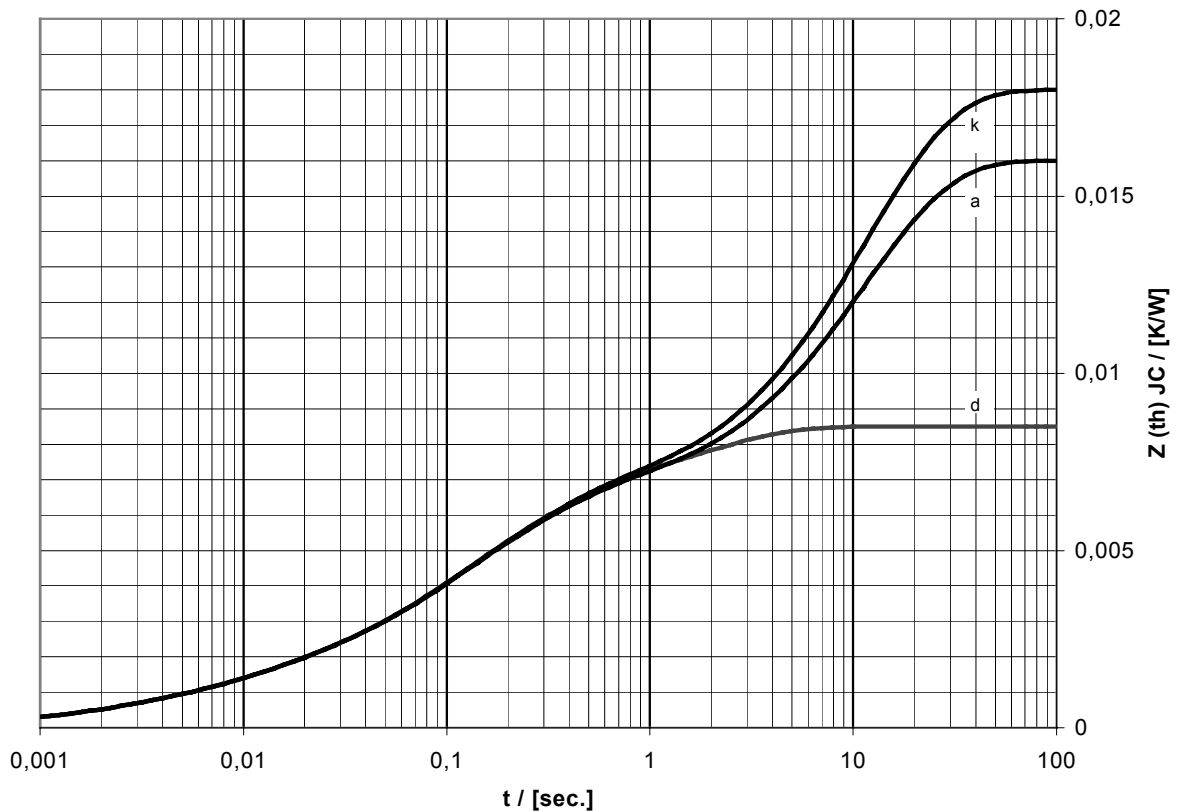
— $t_{vj} = 160^\circ C$
.... $t_{vj} = 25^\circ C$





Transient thermal Impedance for constant-current

	Double side cooled		Anode side cooled		Cathode side cooled	
	r [K/W]	[s]	r [K/W]	[s]	r [K/W]	[s]
1	0,002	1,84	0,0095	11,5	0,0115	11,7
2	0,003	0,24	0,003	0,24	0,003	0,24
3	0,0022	0,071	0,0022	0,071	0,0022	0,071
4	0,0009	0,0097	0,0009	0,0097	0,0009	0,0097
5	0,0004	0,0018	0,0004	0,0018	0,0004	0,0018
Σ	0,0085	-	0,016	-	0,018	-

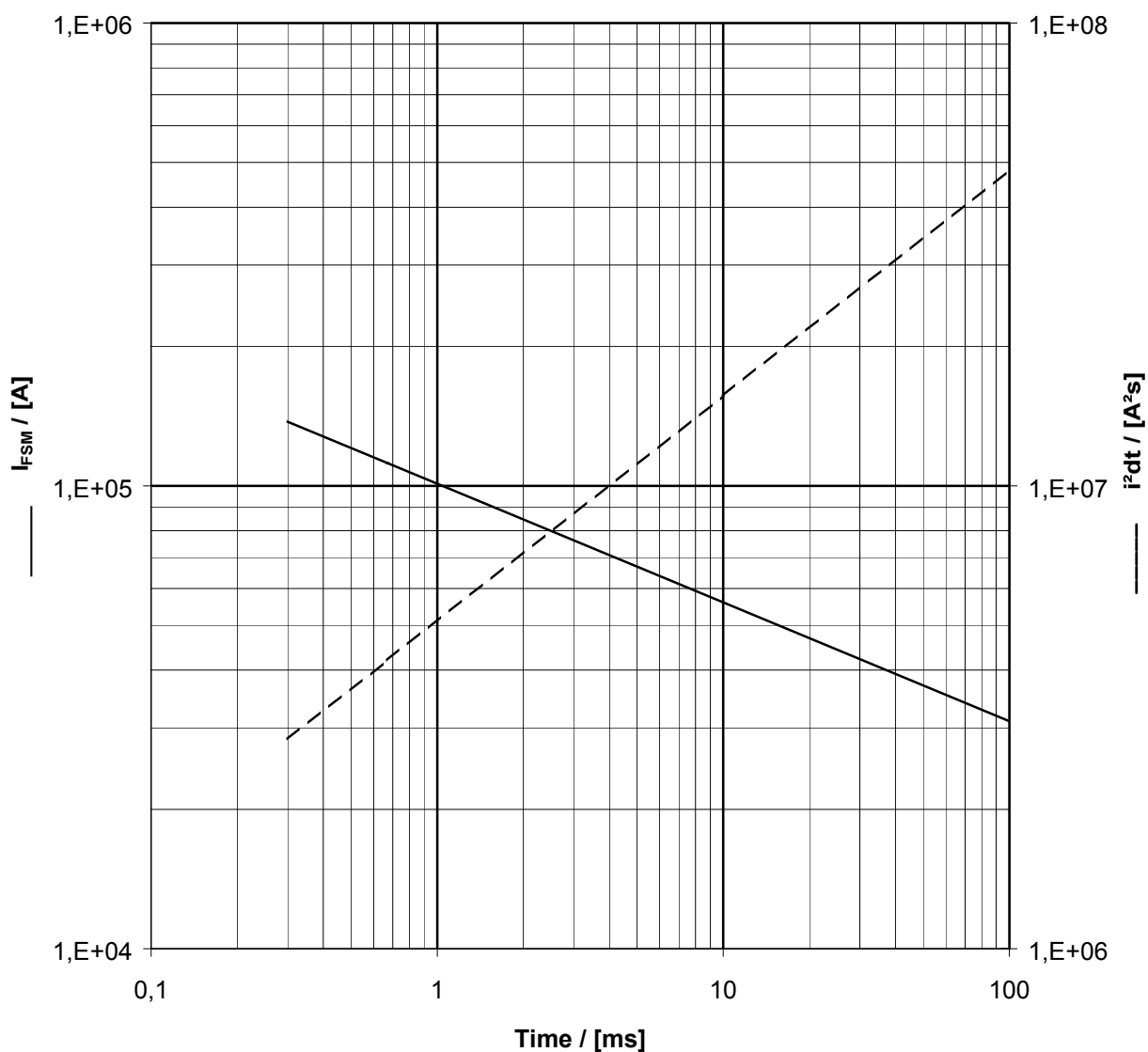


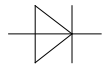


Surge Current Characteristics $I_{FSM} = f(t_p)$

I^2t value $i^2 dt = f(t_p)$

Sine half-wave, $t_{vj} = 160^\circ C, v_R = 0$





Sperrverzögerungsladung $Q_r = f(-di/dt)$
Reverse recovered charge

$t_{vj} = 160^\circ \text{C}$, $I_{FM} = 1500 \text{ A}$, $v_R = 0,5 V_{RRM}$
 $C = 4,7 \mu\text{F}$, $R = 8,2 \Omega$

— max.
..... typ.

